**Supporting Information** 

## Choline Chloride-Modified SnO<sub>2</sub> Achieving High Output Voltage in MAPbI<sub>3</sub> Perovskite Solar Cells

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Figure S1. XRD patterns of perovskites were deposited on SnO<sub>2</sub> and Chol-SnO<sub>2</sub>.



Figure S2. Grain size distribution of perovskite films deposited on a) SnO<sub>2</sub>, b) Chol-SnO<sub>2</sub>.



Figure S3. AFM images: Surface morphology of perovskite film deposited on a, c) SnO<sub>2</sub> and b, d)

Chol-SnO<sub>2</sub>.



Figure S4. XPS fine spectrum of a) N 1s and b) Cl 2p on the SnO<sub>2</sub> and Chol-SnO<sub>2</sub>.



Figure S5. XPS curve of SnO<sub>2</sub> and Chol-SnO<sub>2</sub> at O 1s level.



Figure S6. UV-vis spectra of SnO<sub>2</sub> and Chol-SnO<sub>2</sub>.



Figure S7. J-V curves of the devices having a) SnO<sub>2</sub> and b) Chol-SnO<sub>2</sub> for forward and reverse

scanning.

Samples	$E_{g}(eV)$	$E_{\text{cutoff}} \left( \text{eV} \right)$	$E_{\rm F}({ m eV})$	$E_{\rm VB}~({\rm eV})$	$E_{\rm CB}~({\rm eV})$
SnO <sub>2</sub>	3.64	16.34	4.88	7.90	4.26
Chol-SnO <sub>2</sub>	3.81	16.59	4.63	7.80	3.99

**Table S1.** Band gaps ( $E_g$ ), secondary–electron cutoff ( $E_{cutoff}$ ), fermi level ( $E_F$ ), valence band ( $E_{VB}$ ) and conduction band ( $E_{CB}$ ) for bare SnO<sub>2</sub> film and Chol-SnO<sub>2</sub> film.

In order to get the Fermi level ( $E_F$ ), we use  $E_F=E_{cutoff} - 21.22$  eV, where  $E_{cutoff}$  is cutoff binding energy, and 21.22 eV is emission energy from He irradiation. The  $E_{cutoff}$  of SnO<sub>2</sub> and Chol-SnO<sub>2</sub> film are 16.34 and 16.59 eV, respectively. The  $E_F$  of SnO<sub>2</sub> and Chol-SnO<sub>2</sub> film are calculated as -4.88 and -4.63 eV, respectively. The  $E_{VB}$  of SnO<sub>2</sub> and Chol-SnO<sub>2</sub> film are -7.90 and -7.80 eV, calculating as  $E_{VB}=E_F-E_{F, edge}$  (Fermi edge). According to the absorption spectrum and Tauc plot, we get the band gap ( $E_g$ ) of SnO<sub>2</sub> (3.64 eV) and the Chol-SnO<sub>2</sub> (3.81 eV). Their  $E_{CB}$  obtained from  $E_g$  and  $E_{VB}$  is -4.26 and -3.99 eV, respectively.

Samples	$A_1$	$ au_1$	$A_2$	$ au_2$	Average decay time $\tau$ (ns) <sup>a</sup>
SnO <sub>2</sub>	0.464	28.07	0.609	366.3	219.9
Chol-SnO <sub>2</sub>	0.208	16.27	0.810	122.1	100.5

**Table S2.** Fitting parameters of bi–exponential decay function in TRPL spectra.

<sup>a</sup> Average decay time is calculated according to the equation:  $\tau = (A_1\tau_1 + A_2\tau_2)/(A_1 + A_2)$ .

Samples	$R_{\rm s}~(\Omega~{ m cm}^2)$	$R_{ m rec}$ ( $\Omega$ cm <sup>2</sup> )
SnO <sub>2</sub>	0.73	$7.94 \times 10^3$
Chol-SnO <sub>2</sub>	1.19	$1.85 \times 10^4$

**Table S3.** The fitted parameters for EIS measurements acquired under dark based on different samples.